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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/566,300	01/25/2006	Ryo Suzuki	OGOSH42USA	2014
270 HOWSON & H	7590 03/20/200 IOWSON LLP	9	EXAMINER	
501 OFFICE C	ENTER DRIVE		LI, JUN	
SUITE 210 FORT WASHII	NGTON, PA 19034		ART UNIT	PAPER NUMBER
			1793	
			MAIL DATE	DELIVERY MODE
			03/20/2009	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Office Action Summary		Applica	ation No.	Applicant(s)	Applicant(s)	
		10/566	,300	SUZUKI, RYO		
		Examir	er	Art Unit		
		JUN LI		1793		
The MA Period for Reply	ILING DATE of this commur	nication appears on	the cover sheet with	n the correspondence a	ddress	
A SHORTENE WHICHEVER - Extensions of time after SIX (6) MON - If NO period for re - Failure to reply wil Any reply received	D STATUTORY PERIOD F IS LONGER, FROM THE M may be available under the provisions THS from the mailing date of this comingly is specified above, the maximum significant the set or extended period for reply by the Office later than three months in adjustment. See 37 CFR 1.704(b).	MAILING DATE OF s of 37 CFR 1.136(a). In no nunication. atutory period will apply and will, by statute, cause the a	THIS COMMUNIC, event, however, may a report will expire SIX (6) MONTI application to become ABA	ATION. Only be timely filed HS from the mailing date of this only NDONED (35 U.S.C. § 133).	,	
Status						
1)⊠ Respons 2a)⊠ This acti 3)□ Since thi	ive to communication(s) file on is FINAL . s application is in condition accordance with the pract	2b)⊡ This action is for allowance exce	_ s non-final. pt for formal matte	•	e merits is	
Disposition of Cla	nims					
4a) Of the 5) ☐ Claim(s) 6) ☑ Claim(s) 7) ☐ Claim(s)	1 is/are pending in the appea above claim(s) is/a is/are allowed. 1 is/are rejected. 1 is/are objected to. 1 are subject to restricts	re withdrawn from				
10)☐ The draw Applicant Replacen	ification is objected to by the ing(s) filed on is/are may not request that any objected to declaration is objected to the control of t	a) accepted or ction to the drawing(sg the correction is req	e) be held in abeyanc uired if the drawing(s	e. See 37 CFR 1.85(a).) is objected to. See 37 C	, ,	
Priority under 35	U.S.C. § 119					
12) Acknowled a) All b 1. Ce 2. Ce 3. Ce ap	edgment is made of a claim Some * c) None of: Partified copies of the priority Partified copies Partifie	documents have b documents have b of the priority docu onal Bureau (PCT R	een received. een received in Ap ments have been n kule 17.2(a)).	plication No eceived in this Nationa	l Stage	
· =	erson's Patent Drawing Review (I osure Statement(s) (PTO/SB/08)	PTO-948)	Paper No(s)	mmary (PTO-413) /Mail Date ormal Patent Application -		

DETAILED ACTION

Status of Application

The objection of is withdrawn due to the applicant's amendments

Claim 1 is amended wherein the addition have resulted in a change of scope the claims.

Claim Rejections - 35 USC § 103

The text of those sections of Title 35, U.S. Code not included in this action can be found in a prior Office action.

1. Claim 1 is rejected under 35 U.S.C. 103(a) as being unpatentable over Takeda (JP09-260139) in view of Watanabe (JP09-316630) and Kodera (JP06-330297).

Takeda teaches a perovskite composition La_{1-x}A_xMnO_z wherein A can be Ca, Ba or Sr and $0.05 \le x \le 0.5$, $2.7 \le z \le 3$ (Clm 1-3), which read onto the recited composition in the instant claim. Takeda further teaches a sputtering target such as a thin film can be formed by this perovskite composition via a sputtering technique (abstract, [00014]). It is to be noted that the range of x and z overlaps with the range of x and α in the instant claim, thus render a prima facie obviousness (See § MPEP 2144.05 [R-5] I).

Takeda fails to specifically teach this target has (1) a relative density not less than 95%, an average crystal grain size is not greater than 100 um , and (2) a resistivity not greater than 10 Ω m.

With respect to (1), Wantanabe teaches a sputtering target can be made from perovskite oxide with a relative density of 95-99%, and purity regulated >4N

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and particle size less than 20 um to prevent target cracking (abstract, , claim 1,[0006]) via controlling pressure and sintering conditions. Wantanabe further discloses the average particle diameter is decreased in order to improve the transverse resilience of said sintered compact ([0008]) and the sintered product is made to have a purity more than 4N or higher in order to prevent the growth of the grains in said sintered compact ([0011]).

It would have been obvious to one of ordinary skill in the art at the time of invention filed to adopt the techniques of Wantanabe to improve the sputtering target made from composition of La_{1-x}A_xMnO₃ as shown by Takeda. One of ordinary skill in the art would have been motivated to do so because controlling the sputtering target properties such as density, purity, particle sizes can minimizing the cracking formation during a high power and high film formation sputtering process as indicated by Wantanabe ([0003],[0006], abstract, Clm1-3).

With respect to (2), Kodera teaches sputtering target of a perovskite oxide can have a resistivity ≤10 Ωm for a dielectric formation (Clm 1, abstract). Kodera further teaches the electrical resistivity can be controlled by the pervoskite oxide compound's oxygen efficiency during sintering process thus provide a stabilized dielectric membrane via sputtering ([0020],[0022],[0023]).

It would have been obvious to one of ordinary skill in the art at the time of invention filed to adopt resistivity of Kodera to improve the sputtering target made from composition of La_{1-x}A_xMnO₃ as shown by Takeda in view of Wantanabe.

One of ordinary skill in the art would have been motivated to do so because controlling the resistivity of sputtering target can help forming a stabilized

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dielectric membrane during sputtering process as shown by Kodera (abstract, Clm1, [0020],[0022],[0023]).

Response to Arguments

2. Applicant's arguments filed on 03/03/2009 with respect to claim 1 have been considered but are most in view of the new ground(s) of rejection.

In response to Applicant's argument about the pervoskite composition in JP'630, examiner find it not persuasive because the general composition with recited formula in the instant claim has already been disclosed in the primary reference such as Bates in previous action and JP'139. It is obvious to adopt similar techniques for controlling pervoskite oxide compound as disclosed in JP'630 to improve the properties for the formed sputtering target during sputtering process. Furthermore, applicants have not provide any evidence to such combination are not possible for one ordinary skill in the art.

Conclusion

3. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire

THREE MONTHS from the mailing date of this action. In the event a first reply is

filed within TWO MONTHS of the mailing date of this final action and the advisory

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action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to JUN LI whose telephone number is (571)270-5858. The examiner can normally be reached on Monday-Friday, 8:00am EST-5:00 pm EST.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Curtis Mayes can be reached on 571-272-1234. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/JUN LI/ Examiner, Art Unit 1793

/J. L./ 03/10/2009

/Melvin Curtis Mayes/ Supervisory Patent Examiner, Art Unit 1793